

60V PNP SILICON PLANAR MEDIUM POWER TRANSISTOR IN SOT89
Features

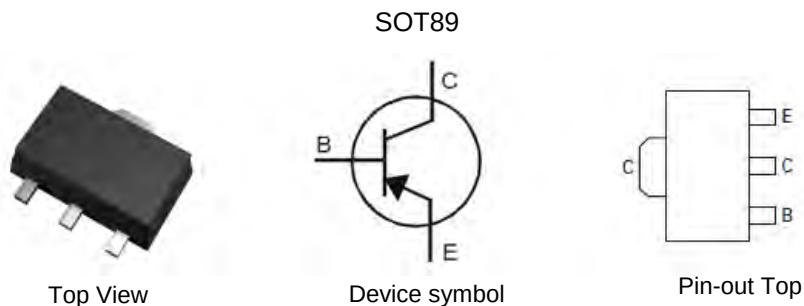
- $BV_{CEO} > -60V$
- High current capability Max Continuous Current $I_C = -4.3A$
- Low saturation voltage $V_{CE(sat)} < -65mV$ @ $I_C = -1A$
- **Lead Free, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free, "Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Application

- Emergency lighting circuits
- Motor driving (including DC fans)
- Backlight inverters
- Power switches
- MOSFET gate drivers

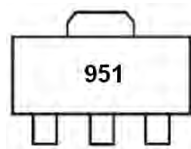
Mechanical Data

- Case: SOT89
- Moisture Sensitivity: Level 1 per J-STD-020
- UL Flammability Rating 94V-0
- Terminals: Matte Tin Finish
- Weight: 0.052 grams (Approximate)


Ordering Information (Note 3 & 4)

Product	Grade	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP2012ZTA	Commercial	951	7	12	1,000
ZXTP2012Z-13R	Commercial	951	7	12	4,000
ZXTP2012ZQTA	Automotive	951	7	12	1,000

- Notes:
1. No purposefully added lead.
 2. Halogen and Antimony Free. Diodes Inc's "Green" Policy can be found on our website at <http://www.diodes.com>
 3. For packaging details, go to our website at <http://www.diodes.com>
 4. Products with Q-suffix are automotive grade

Marking Information


951 = Product Type Marking Code

Maximum Ratings @T_A = 25°C unless otherwise specified

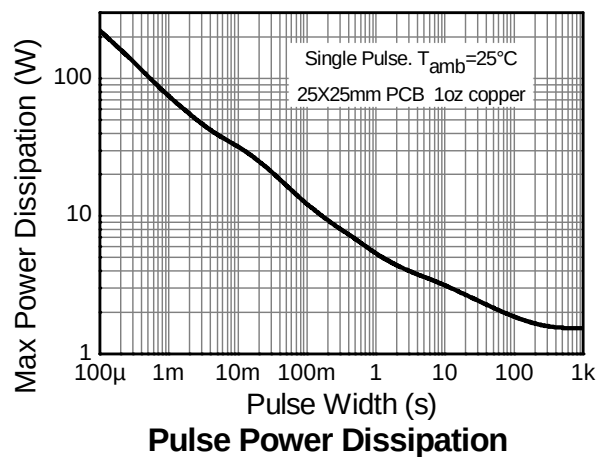
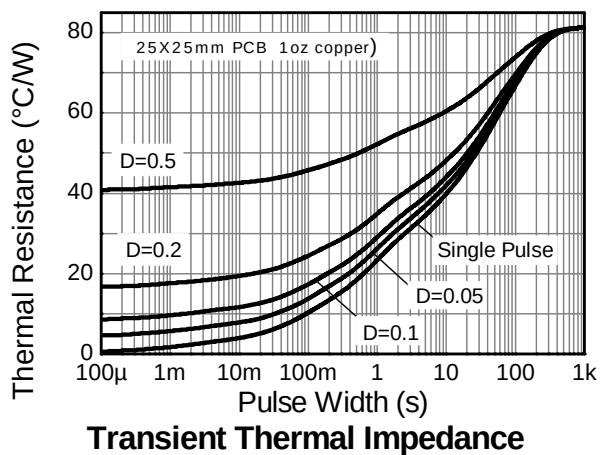
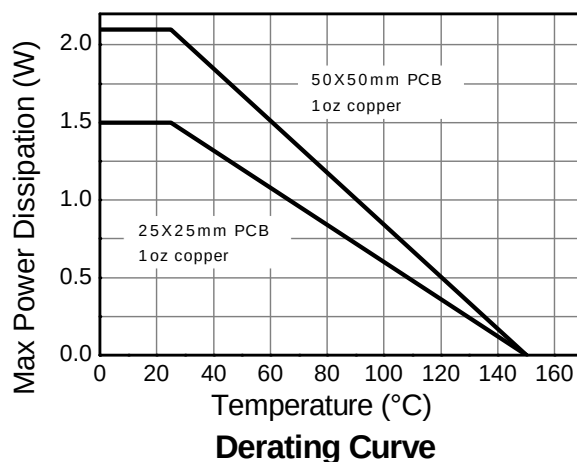
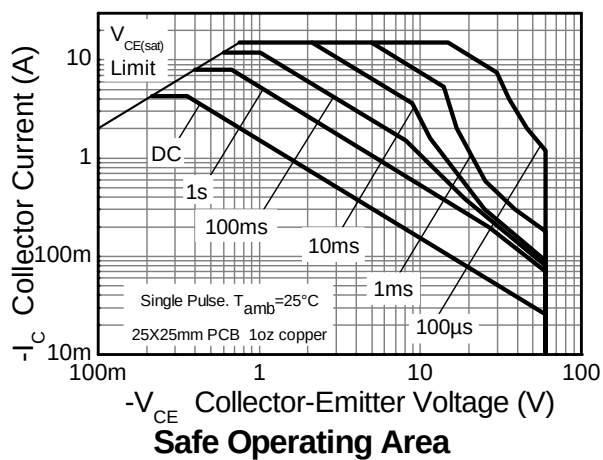
Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current (Note 5)	I _C	-4.3	A
Peak Pulse Current	I _{CM}	-15	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	1.5	W
Linear derating factor		12	mW/°C
Power Dissipation (Note 6)	P _D	2.1	W
Linear derating factor		16.8	mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	83	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	60	°C/W
Thermal Resistance, Junction to Leads (Note 7)	R _{θJL}	3.23	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
6. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
7. Thermal resistance from junction to solder-point (on the exposed collector pad).

Thermal Characteristics

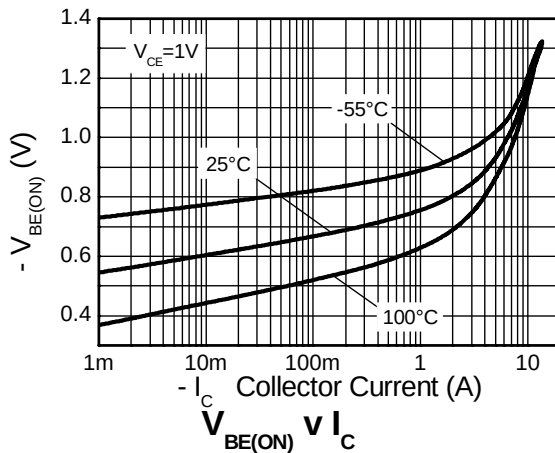
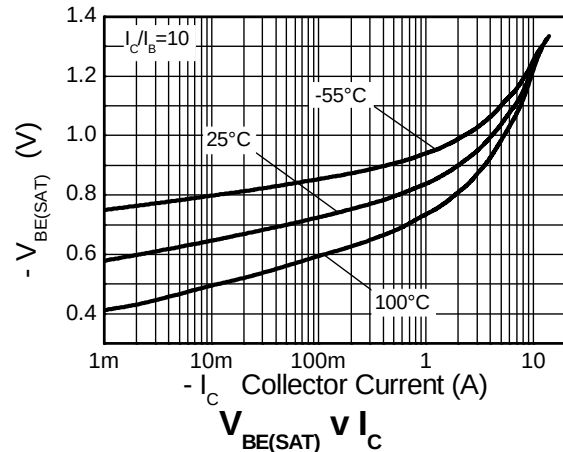
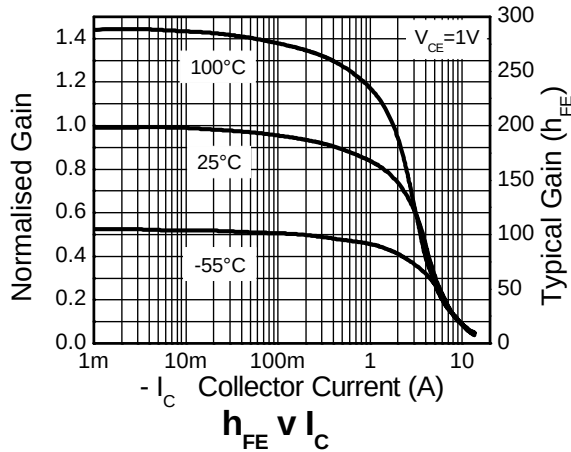
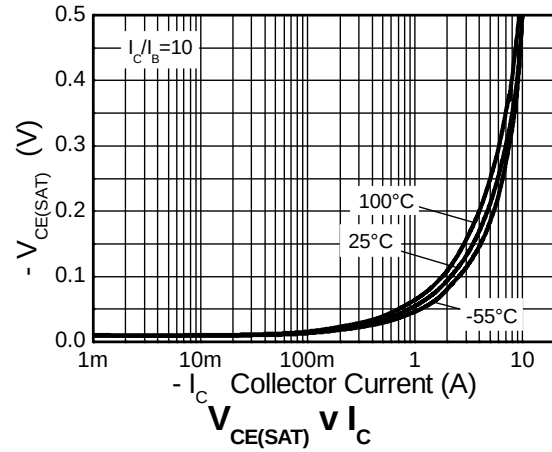
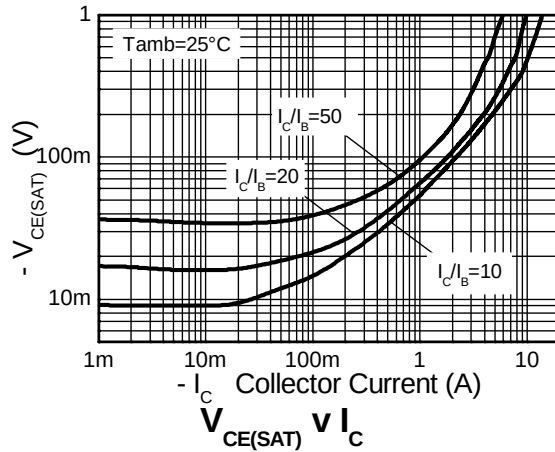


Electrical Characteristics @T_A = 25°C unless otherwise specified

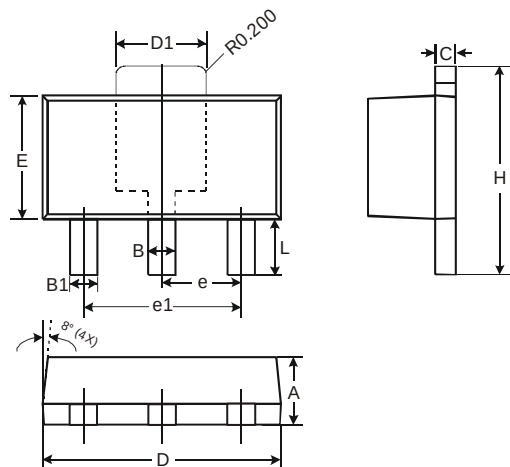
Characteristic	Symbol	Min	Typ.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-120	-	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Notes 8)	BV _{CER}	-100	-120	-	V	I _C = -1μA, R _B ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Notes 8)	BV _{CEO}	-60	-80	-	V	I _C = -10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	-	V	I _E = -100μA
Collector Cutoff Current	I _{CBO}	-	< -1	-20 -500	nA nA	V _{CB} = -80V V _{CB} = -80V, T _A = 100°C
Collector Cutoff Current	I _{CER} R ≤ 1kΩ	-	< -1	-20 -500	nA nA	V _{CB} = -80V V _{CB} = -80V, T _A = 100°C
Emitter Cutoff Current	I _{EBO}	-	< -1	-10	nA	V _{EB} = -6V
DC current transfer Static ratio (Notes 8)	h _{FE}	100 100 45 10	250 200 90 25	300		I _C = -10mA, V _{CE} = -1V I _C = -2A, V _{CE} = -1V I _C = -5A, V _{CE} = -1V I _C = -10A, V _{CE} = -1V
Collector-Emitter Saturation Voltage (Notes 8)	V _{CE(sat)}	-	-14 -50 -75 -160	-20 -65 -110 -215	mV	I _C = -100mA, I _B = -10mA I _C = -1A, I _B = -100mA I _C = -2A, I _B = -200mA I _C = -5A, I _B = -500mA
Base-Emitter Saturation Voltage (Notes 8)	V _{BE(sat)}	-	-950	-1050	mV	I _C = -5A, V _{CE} = -1V
Base-Emitter Turn-on Voltage (Notes 8)	V _{BE(on)}	-	-840	-950	mV	I _C = -5A, V _{CE} = -1V
Transitional Frequency (Notes 8)	f _T	-	120	-	MHz	I _C = -100mA, V _{CE} = -10V, f = 50MHz
Output capacitance	C _{obo}	-	48	-	pF	V _{CB} = -10V, f = 1MHz,
Switching Time	t _{ON}	-	39	-	ns	V _{CC} = -10V, I _C = -1A, I _{B1} = I _{B2} = -100mA
	t _{OFF}		370			

Notes: 8. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

Typical Electrical Characteristics

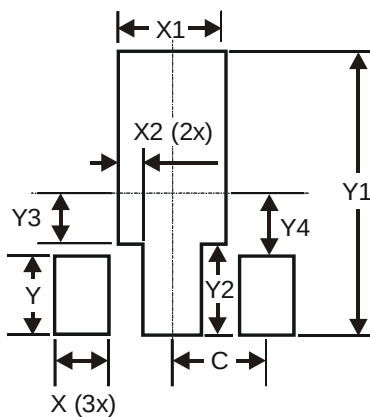


Package Outline Dimensions



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.43
D	4.40	4.60
D1	1.52	1.83
E	2.29	2.60
e	1.50 Typ	
e1	3.00 Typ	
H	3.94	4.25
L	0.89	1.20
All Dimensions in mm		

Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500

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